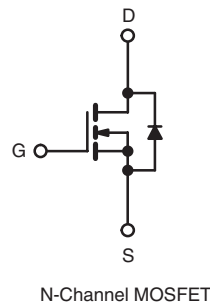


Power MOSFET

| PRODUCT SUMMARY | |
|---------------------------|------------------------------|
| V_{DS} (V) | 250 |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 10\text{ V}$ 0.060 |
| Q_g (Max.) (nC) | 210 |
| Q_{gs} (nC) | 34 |
| Q_{gd} (nC) | 94 |
| Configuration | Single |



FEATURES

- Advanced Process Technology
- Dynamic dV/dt Rating
- 175 °C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available



Available
RoHS*
 COMPLIANT

DESCRIPTION

Fifth generation Power MOSFETs from Vishay utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole.

| ORDERING INFORMATION | |
|----------------------|-----------------------------|
| Package | TO-247 |
| Lead (Pb)-free | IRFP264NPbF SiHFP264N-E3 |
| SnPb | IRFP264N SiHFP264N |

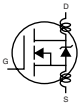

| ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | |
|--|----------------------------------|-----------------------------------|---------------------|
| PARAMETER | SYMBOL | LIMIT | UNIT |
| Drain-Source Voltage | V_{DS} | 250 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current | V_{GS} at 10 V | $T_C = 25\text{ }^\circ\text{C}$ | 44 |
| | | $T_C = 100\text{ }^\circ\text{C}$ | 31 |
| Pulsed Drain Current ^a | I_{DM} | 170 | A |
| Linear Derating Factor | | 2.6 | W/ $^\circ\text{C}$ |
| Single Pulse Avalanche Energy ^b | E_{AS} | 520 | mJ |
| Repetitive Avalanche Current ^a | I_{AR} | 25 | A |
| Repetitive Avalanche Energy ^a | E_{AR} | 38 | mJ |
| Maximum Power Dissipation | $T_C = 25\text{ }^\circ\text{C}$ | P_D | 380 |
| Peak Diode Recovery dV/dt^c | dV/dt | 8.7 | V/ns |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to + 175 | $^\circ\text{C}$ |
| Soldering Recommendations (Peak Temperature) | for 10 s | 300 ^d | |
| Mounting Torque | 6-32 or M3 screw | 10 | lbf · in |
| | | 1.1 | N · m |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 1.7\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 25\text{ A}$, $V_{GS} = 10\text{ V}$ (see fig. 12).
- $I_{SD} \leq 25\text{ A}$, $dI/dt \leq 500\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 175\text{ }^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS | | | | |
|-------------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 40 | °C/W |
| Case-to-Sink, Flat, Greased Surface | R_{thCS} | 0.24 | - | |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 0.39 | |

| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|--|---------------------|---|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$ | 250 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | - | 0.30 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 2.0 | - | 4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 250\text{ V}$, $V_{GS} = 0\text{ V}$ | - | - | 25 | μA |
| | | $V_{DS} = 200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ $I_D = 25\text{ A}^b$ | - | - | 0.060 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 25\text{ V}$, $I_D = 25\text{ A}^b$ | 29 | - | - | S |
| Dynamic | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5 | - | 3860 | - | pF |
| Output Capacitance | C_{oss} | | - | 480 | - | |
| Reverse Transfer Capacitance | C_{rss} | | - | 110 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$ $I_D = 25\text{ A}$, $V_{DS} = 200\text{ V}$, see fig. 6 and 13 | - | - | 210 | nC |
| Gate-Source Charge | Q_{gs} | | - | - | 34 | |
| Gate-Drain Charge | Q_{gd} | | - | - | 94 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 30\text{ V}$, $I_D = 25\text{ A}$, $R_G = 1.8\text{ }\Omega$, $V_{GS} = 10\text{ V}$, see fig. 10 ^b | - | 17 | - | ns |
| Rise Time | t_r | | - | 62 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 52 | - | |
| Fall Time | t_f | | - | 53 | - | |
| Internal Drain Inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact  | - | 5.0 | - | nH |
| Internal Source Inductance | L_S | | - | 13 | - | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 44 | A |
| Pulsed Diode Forward Current ^a | I_{SM} | | - | - | 170 | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}$, $I_S = 25\text{ A}$, $V_{GS} = 0\text{ V}^b$ | - | - | 1.3 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}$, $I_F = 25\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$ | - | 270 | 400 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | - | 2.7 | 4.1 | μC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

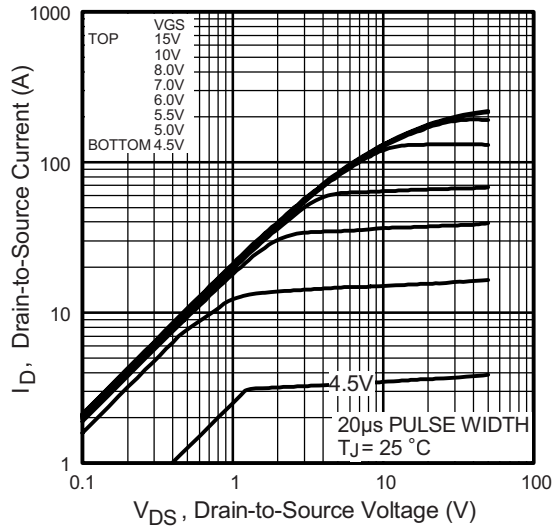


Fig. 1 - Typical Output Characteristics

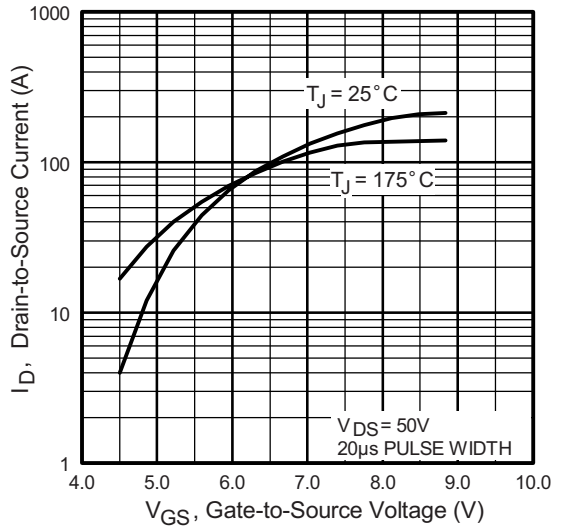


Fig. 3 - Typical Transfer Characteristics

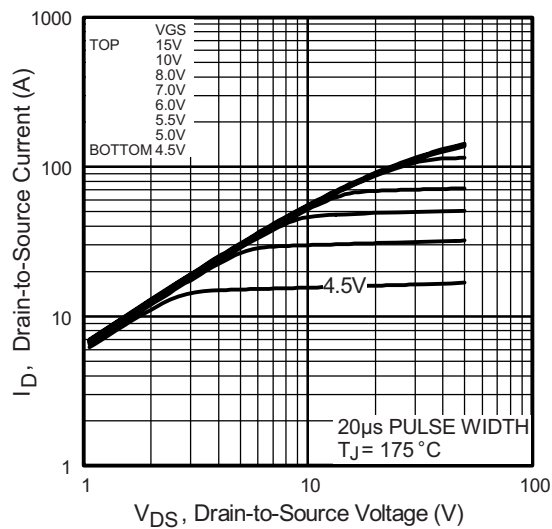


Fig. 2 - Typical Output Characteristics

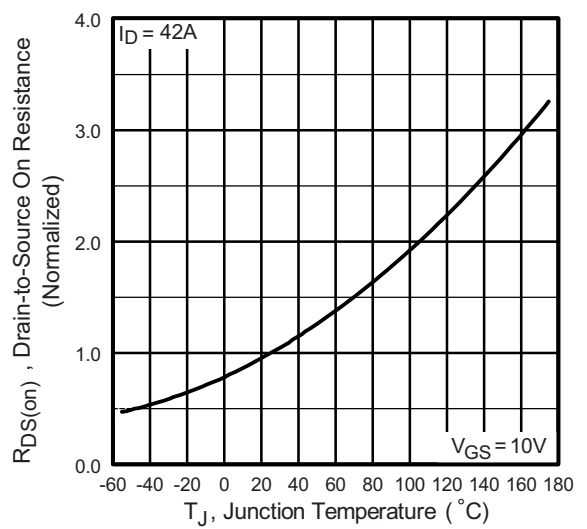


Fig. 4 - Normalized On-Resistance vs. Temperature

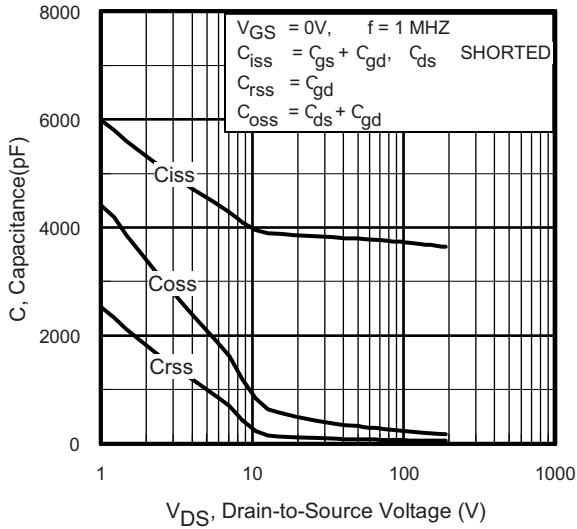


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

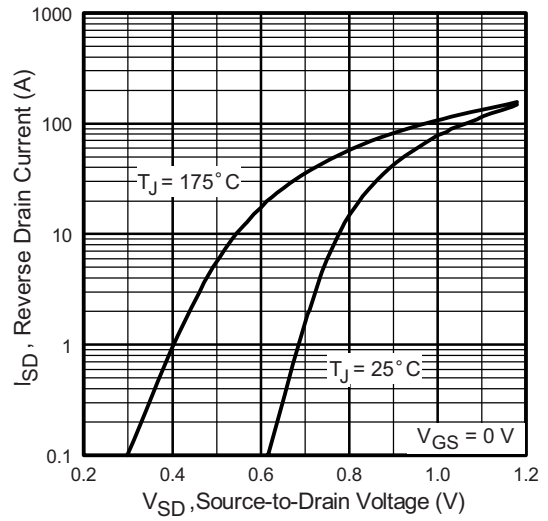


Fig. 7 - Typical Source-Drain Diode Forward Voltage

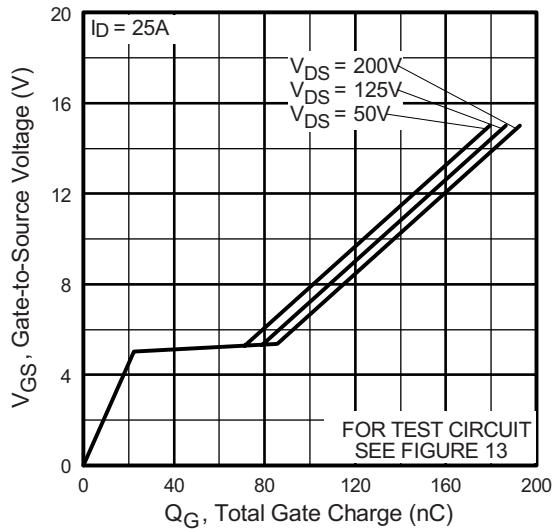


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

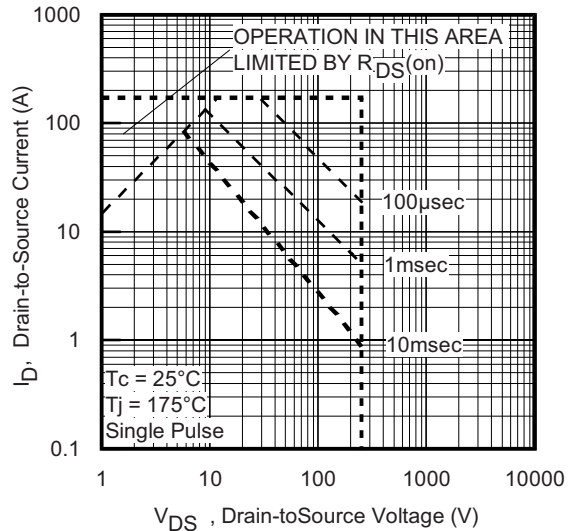


Fig. 8 - Maximum Safe Operating Area

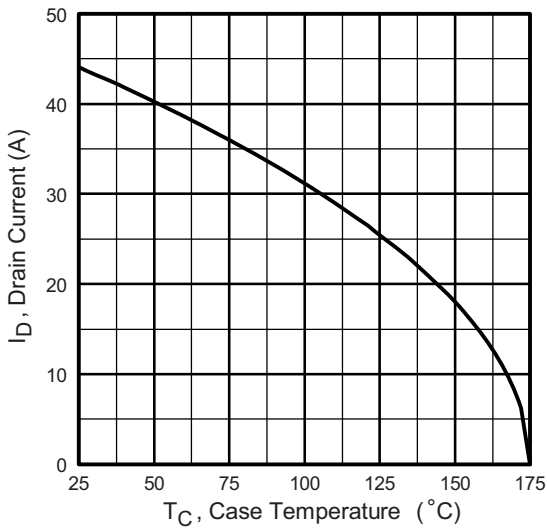


Fig. 9 - Maximum Drain Current vs. Case Temperature

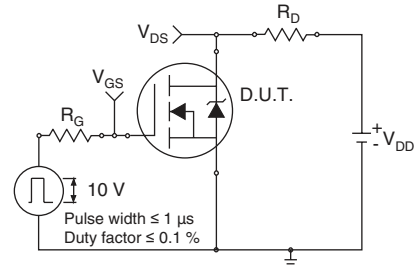


Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms

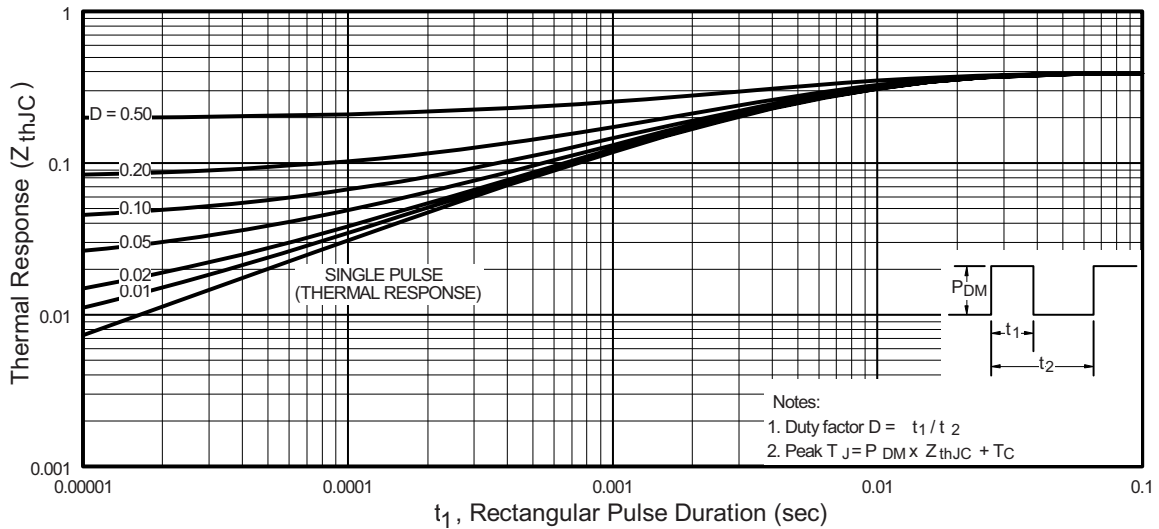


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

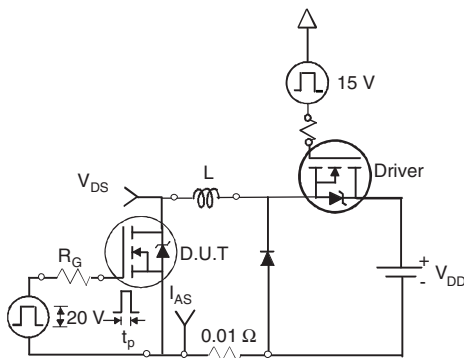


Fig. 12a - Unclamped Inductive Test Circuit

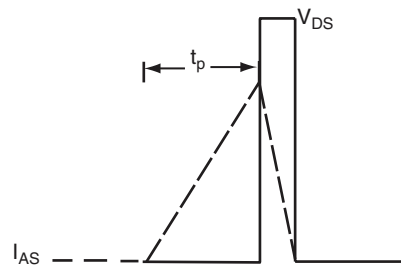


Fig. 12b - Unclamped Inductive Waveforms

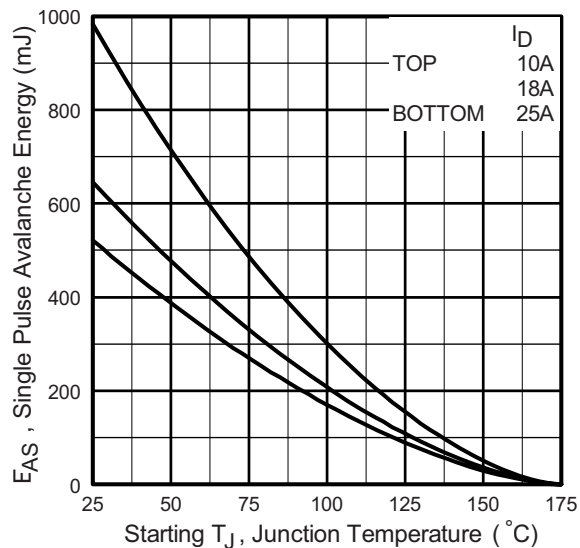


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

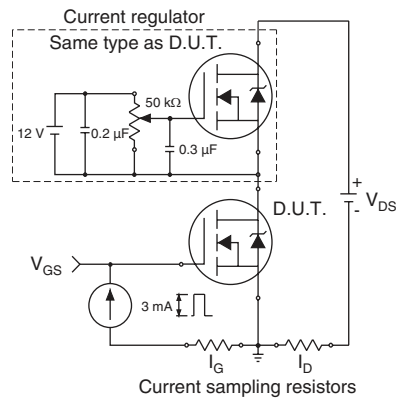
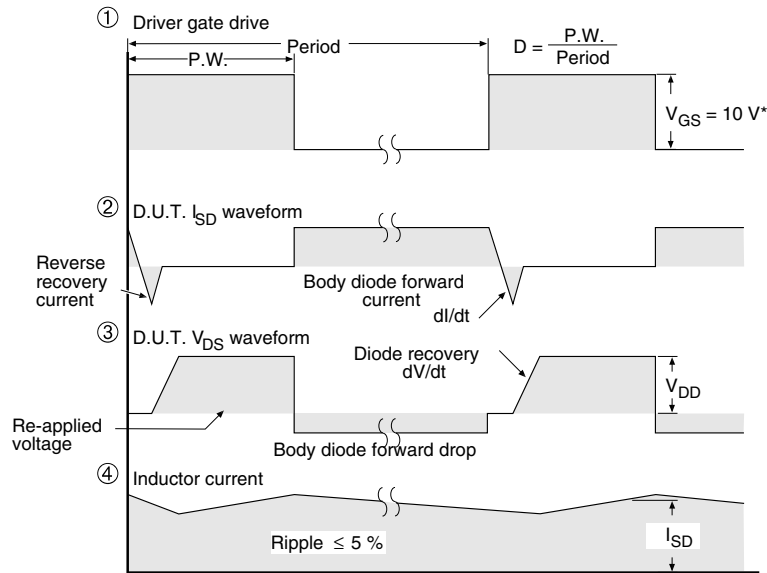
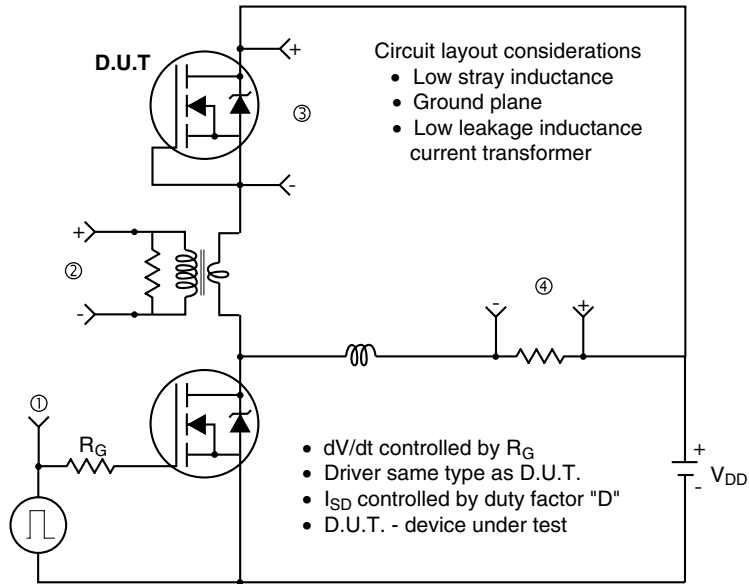


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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